

## AMENDMENTS TO THE CLAIMS

Claims 1-11. (Canceled).

12. (Currently Amended) An electric device comprising: a first elongated nanowire on an insulating surface and a second elongated nanowire on said insulating surface at a right angle ~~angles~~ to said first elongated nanowire and separated therefrom by a gap of between 0.4 nm and 10 nm.

13. (Original) The electric device of Claim 12 wherein said first and second nanowires form a transistor having a source, drain, and gate, and wherein said first nanowire has first and second ends; said first end of said first nanowire forming said source, said second end of said first nanowire forming said drain, and said second nanowire forming said gate.

14. (Currently Amended) The electric ~~electrical~~ device of Claim 12 wherein said first elongated nanowire comprises a semiconductor chosen from the group consisting of Si, Ge,  $\text{Ge}_x\text{Si}_{1-x}$  where  $0 < x < 1$ , GaAs, InAs, AlGaAs, InGaAs, [[AlGaAs,]] GaN, InN, AlN, AlGaN, and InGaN.

15. (Currently Amended) The electric ~~electrical~~ device of Claim 12 wherein said gap is filled with a material that stores electrical charge.

16. (Currently Amended) The electric ~~electrical~~ device of Claim 12 wherein said gap is filled with a material having electric dipole moment.

17. (Currently Amended) The ~~electric electrical~~ device of Claim 12 wherein said first and second nanowires form a two-electrode memory switching device, said first nanowire forming ~~firming~~ the first electrode of said switching device and said second nanowire forming the second electrode of said switching device.